

Fig. 1 (PRIOR ART)

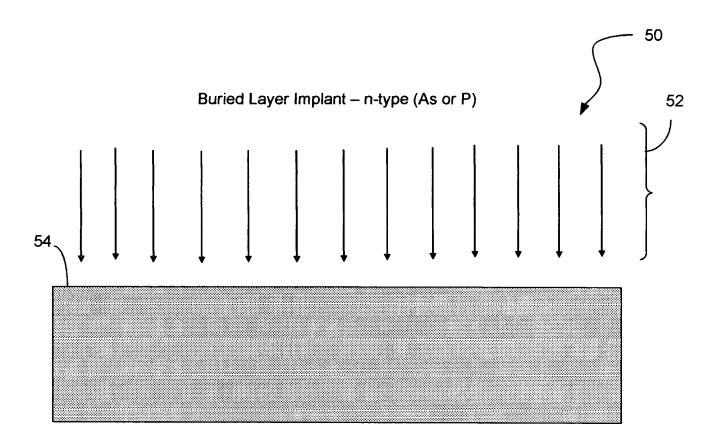


Fig. 2

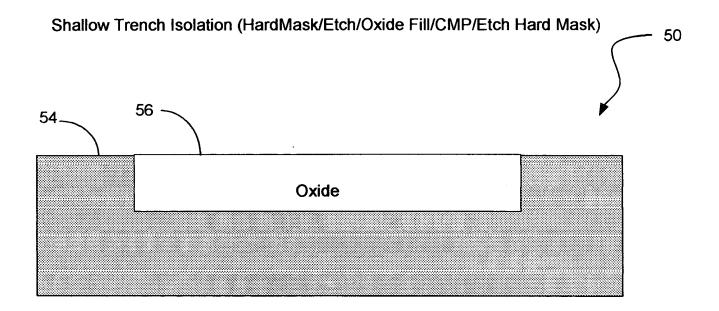


Fig. 3

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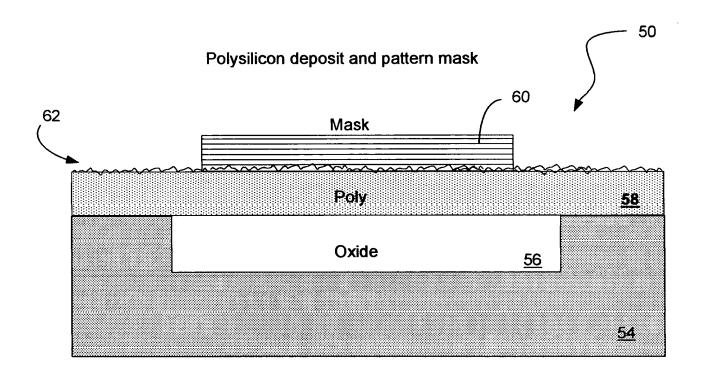
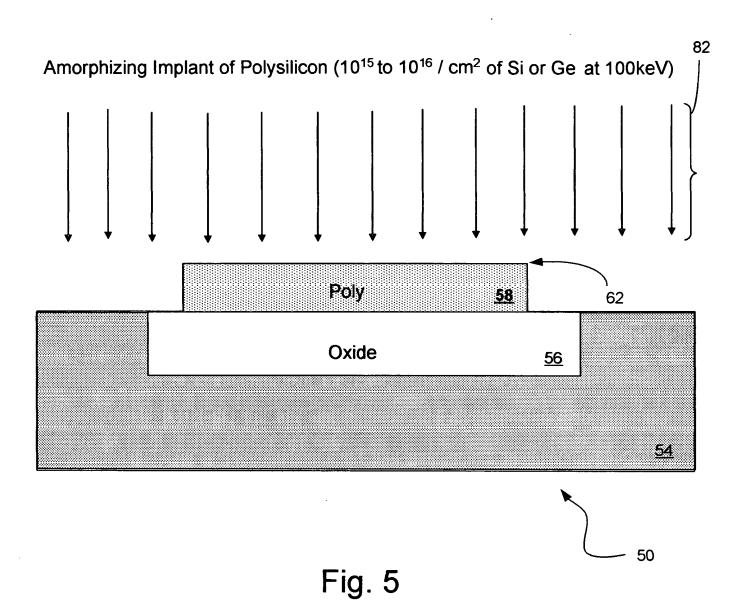


Fig. 4

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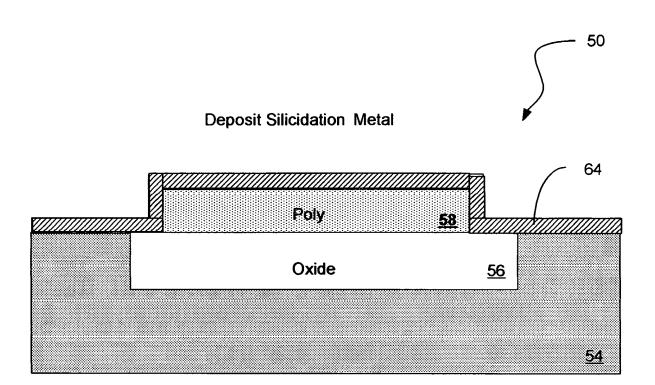


Fig. 6a

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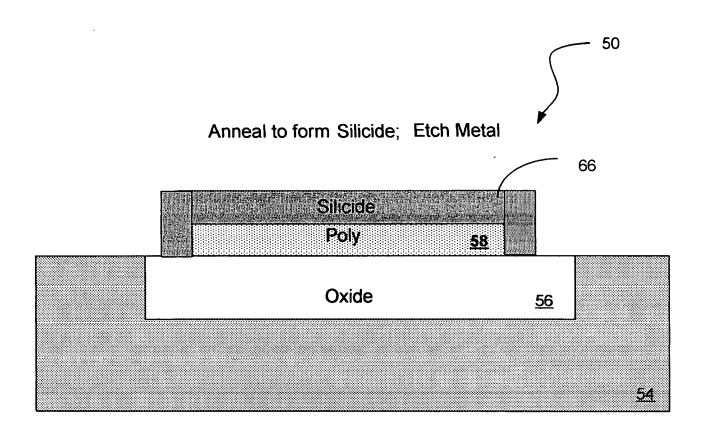


Fig. 6b

## Deposit Dielectric Layer (Oxide or Nitride 500 to 5000 Angstroms)

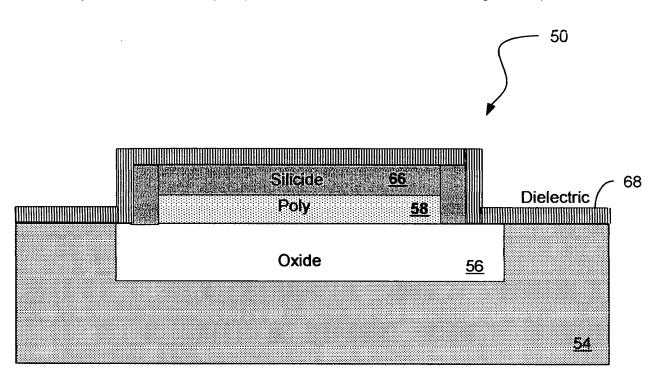


Fig. 7

## Deposit Top Metal Plate (Aluminum/Copper with TiN Barrier Layer); Mask and Etch Capacitor Metal 50 72 Mask 70 68 Sificide .... 66 Poly <u>58</u> Oxide

<u>56</u>

<u>54</u>

Fig. 8

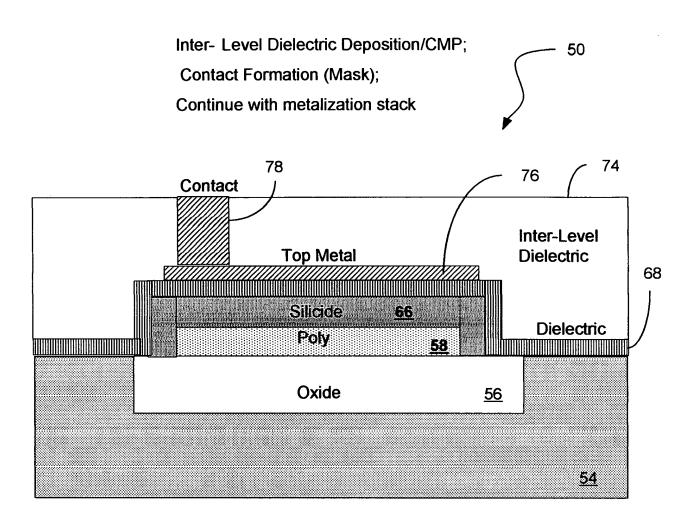


Fig. 9

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